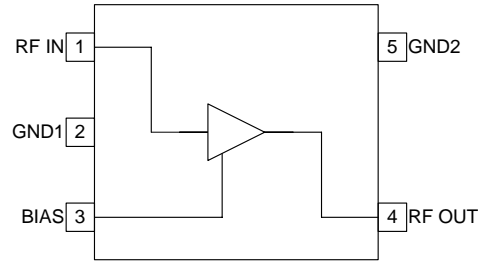


Features

- Low Noise and High Intercept Point
- Adjustable Bias Current
- Power Down Control
- Single 2.7V to 5.0V Power Supply
- 0.4GHz to 4 GHz Operation
- SOT 5-Lead Package

Applications

- WLAN LNA/Driver
- GPS LNA
- CDMA PCS LNA
- Low Noise Transmit Power Amplifier
- General Purpose Amplification
- Driver Amplifier for TX Power Amplifier



Functional Block Diagram

Product Description

The RF2373 is a low noise amplifier with a high dynamic range designed for WLAN, WiMAX, and digital cellular applications. The device functions as an outstanding front end low noise amplifier or driver amplifier in the transmit chain of digital subscriber units where low transmit noise power is a concern. When used as an LNA, the bias current can be set externally. When used as a PA driver, the IC can operate directly from a single cell Li-ion battery and includes a power down feature that can be used to completely turn off the device. The IC is featured in a standard SOT 5-lead plastic package.

Ordering Information

RF2373PCK-414 Fully Assembled Evaluation Board with 5 Sample Parts

Optimum Technology Matching® Applied

- | | | | |
|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

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Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +6.0	V _{DC}
Bias Voltage, V _{BIAS}	≤V _{CC}	V _{DC}
Input RF Level at F<2.3GHz	+5 (see note)	dBm
Input RF Level at F>2.3GHz	+10 (see note)	dBm
Current Drain, I _{CC}	32	mA
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

NOTE: Exceeding any one or a combination of the above maximum rating limits may cause permanent damage. Input RF transients to +15dBm will not harm the device. For sustained operation at inputs ≥+5dBm, a small dropping resistor is recommended in series with the V_{CC} in order to limit the current due to self-biasing to <32mA. Furthermore, while the LNA is in Bypass Mode, and for sustained operation at the input, +10dBm is the maximum recommended power level for Frequencies above 2300MHz. +5dBm is the maximum recommended power level for Frequencies <2300MHz.



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

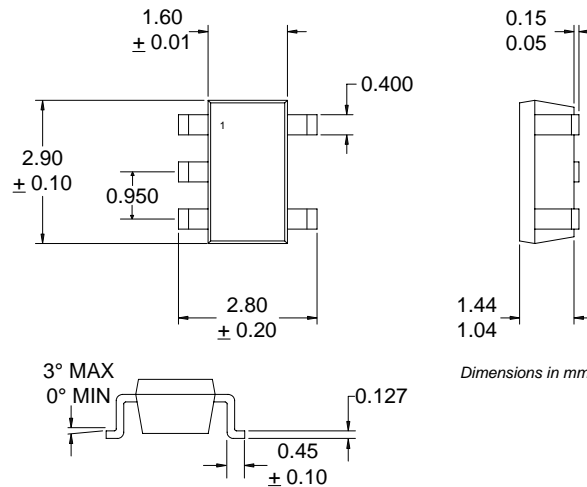
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					25 °C, V _{CC} =3.3V, at typical frequencies unless otherwise specified
Supply Voltage (V _{CC})	2.7	3.3	5.0	V	
Bias Voltage (V _{BIAS})	2.7	3.3	5.0	V	
RF Frequency Range	400		3800	MHz	
Power Down Current			10	μA	V _{BIAS} =0V
Isolation		23		dB	
Current Drain (LNA)	8	14	19	mA	Bias Resistor (R1)=560Ω
IP2		55		dBm	
Cellular Low Noise Amplifier					
Frequency	820	880	960	MHz	
Gain		21.5		dB	
Noise Figure		1.1		dB	
IIP3		-1		dBm	
IP1dB		-11		dBm	
GPS Low Noise Amplifier					
Frequency		1575		MHz	
Gain		19.0		dB	
Noise Figure		1.1		dB	
IIP3		5		dBm	
IP1dB		-6		dBm	

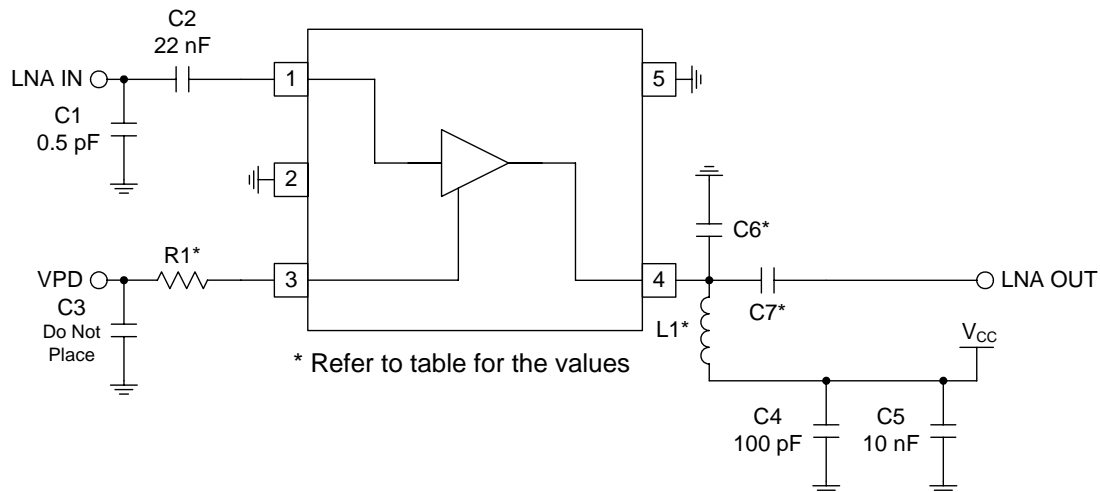
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
W-CDMA Low Noise Amplifier					
Frequency Range	1920	2045	2170	MHz	
Gain		17.5		dB	
Noise Figure		1.2		dB	
IIP3		8		dBm	
IP1dB		-6		dBm	
WLAN Low Noise Amplifier					
Frequency	2400	2450	2500	MHz	
Gain	13.0	15.0	17.0	dB	
Noise Figure		1.3	1.5	dB	
IIP3	7.5	9.5		dBm	
Input P1dB		-3.5		dBm	
WiMAX Low Noise Amplifier					
Frequency	3100	3500	3800	MHz	
Gain		12.5		dB	
Noise Figure		1.5		dB	
IIP3		10		dBm	
Input P1dB		3		dBm	
W-CDMA Driver					
Frequency Range	1920	2045	2170	MHz	V _{CC} =5.0V
Gain		17.5		dB	
Noise Figure		1.3		dB	
OIP3		25		dBm	
OP1dB		14		dBm	
WLAN Driver					
Frequency	2400	2450	2500	MHz	V _{CC} =5.0V
Gain		15.5		dB	
Noise Figure		1.4	1.6	dB	
OIP3		25		dBm	
OP1dB		14		dBm	

Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This pin is DC coupled.	
2	GND1	Ground connection. For best performance, keep traces physically short and connect immediately to ground plane.	
3	BIAS	This pin is used to control the bias current. An external resistor can be used to set the bias current for any V_{BIAS} voltage. See table with evaluation board schematic.	
4	RF OUT	Amplifier output pin. This pin is an open-collector output. It must be biased to V_{CC} through a choke or matching inductor. This pin is typically matched to 50Ω with a shunt bias/matching inductor and series blocking/matching capacitor. Refer to application schematics.	
5	GND2	Ground connection. For best performance, keep traces physically short and connect immediately to ground plane.	

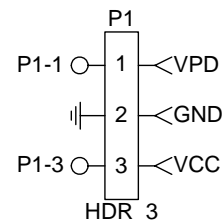
Package Drawing SOT 5-Lead



Evaluation Board Schematic



Component	Cellular 900 MHz	GPS 1575 MHz	PCS 1950 MHz	W-CDMA 2140 MHz	WLAN 2450 MHz
L1 (nH)	3.9	2.7	2.7	2.7	2.2
C6 (pF)	4.3	1.5	0.5	DNP	DNP
C7 (pF)	2.0	1.2	1.0	1.0	1.0

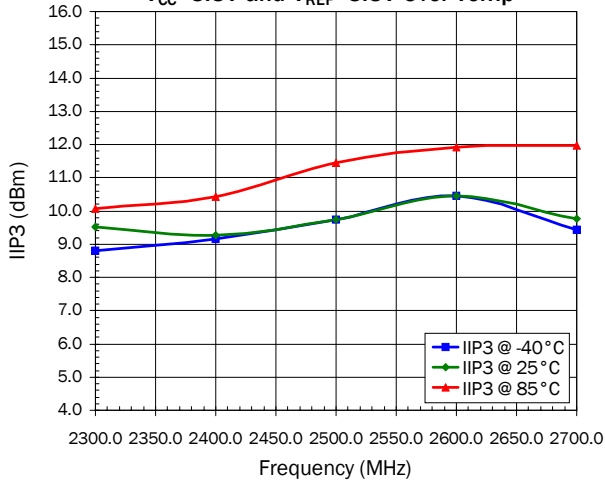


V _{PD}	I _{CC}				
	R1 = 300 Ω	R1 = 430 Ω	R1 = 560 Ω	R1 = 1 kΩ	R1 = 1.5 kΩ
2.7	12	9	7	5	4
3.0	16	12	9	6	5
3.3	20	15	11	7	5
3.6	25	19	14	8	6
4.0	31	24	18	10	7
4.5	Over Limit	31	23	13	8
5.0	Over Limit	Over Limit	29	16	10

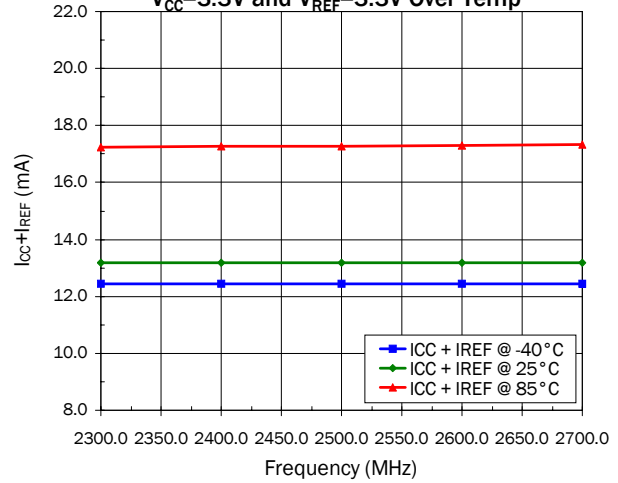
Note: V_{CC} set to 3.3 V. I_{CC} only slightly dependent on V_{CC}.

WiBRO/WLAN DATA

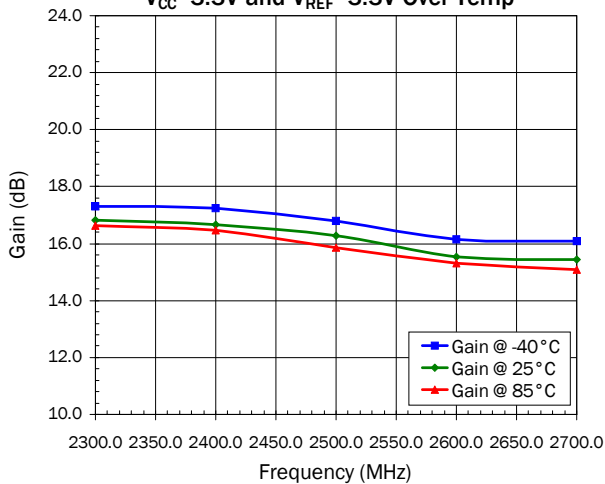
IIP3 @ WLAN Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



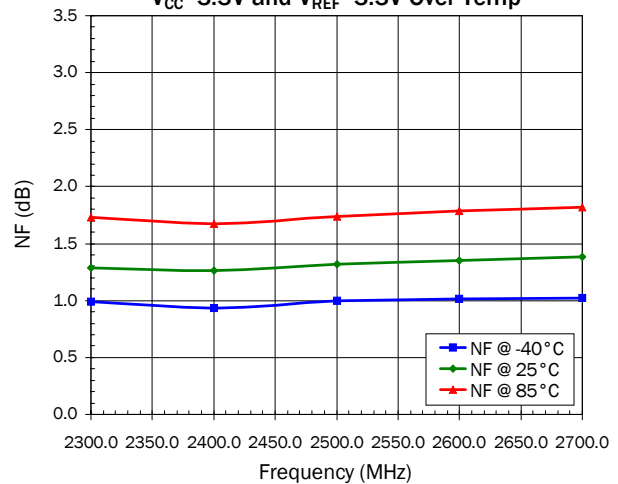
$I_{CC}+I_{REF}$ @ WLAN Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



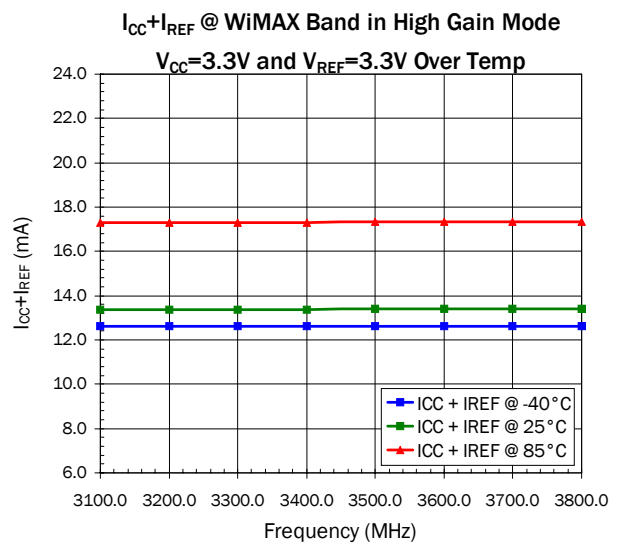
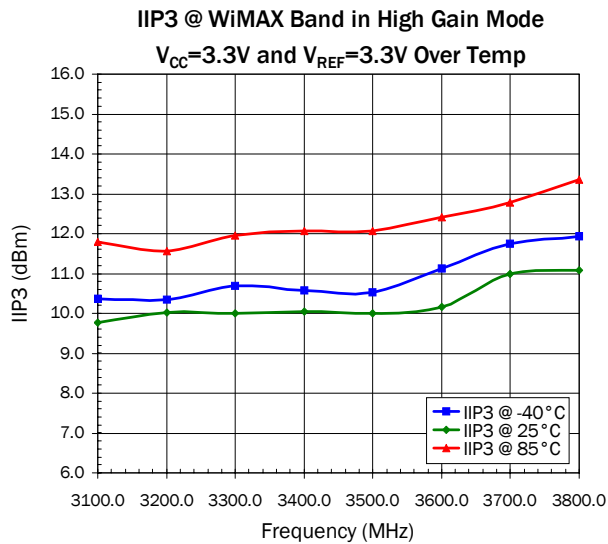
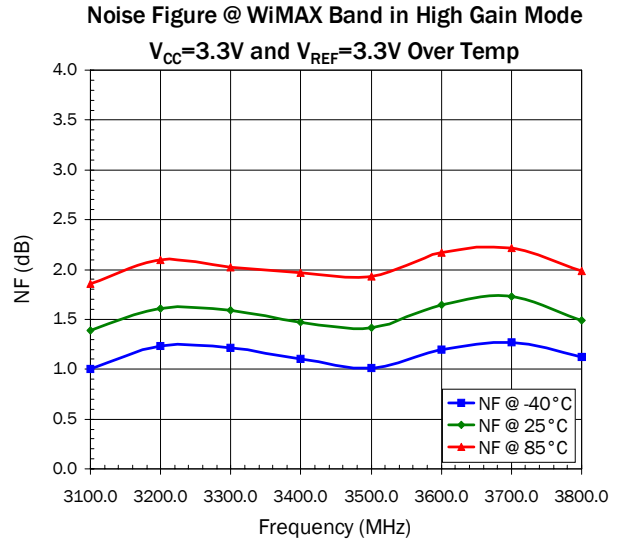
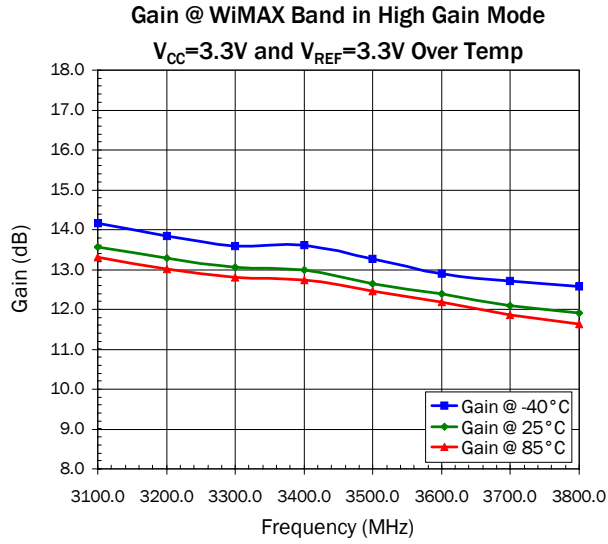
Gain @ WLAN Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



Noise Figure @ WLAN Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp

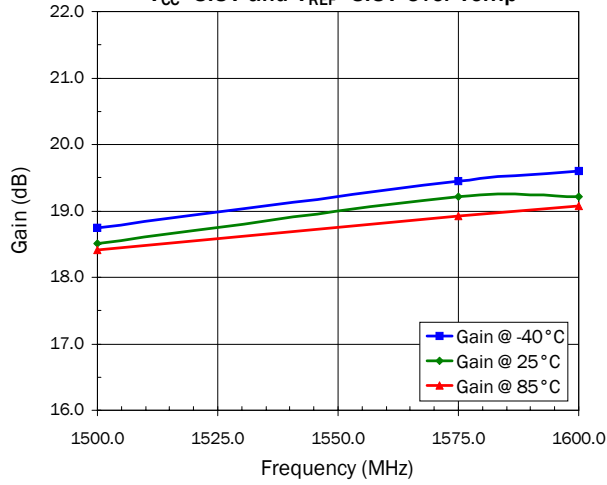


WiMAX DATA

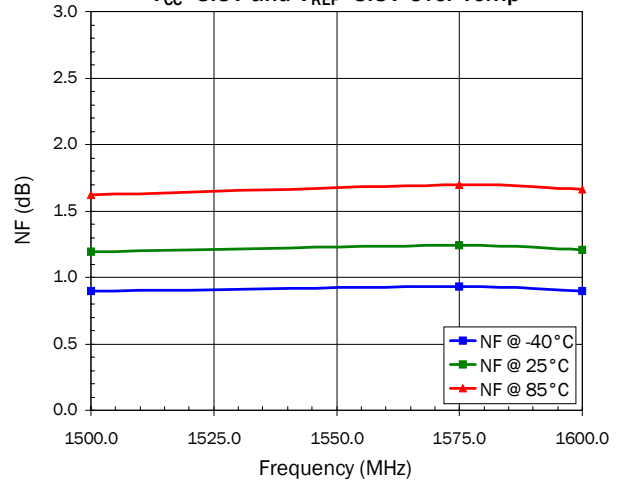


GPS DATA

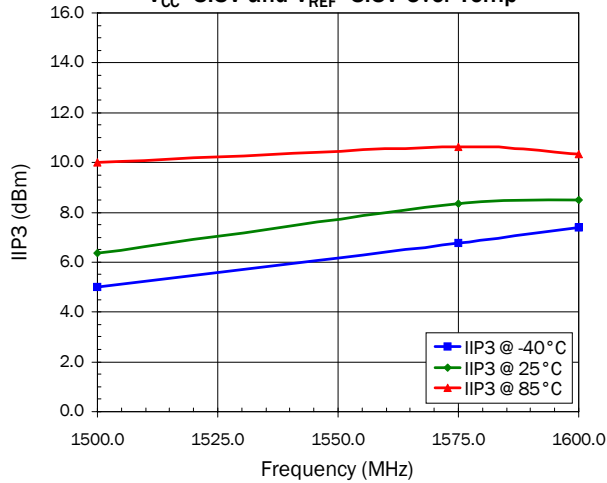
Gain @ GPS Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



Noise Figure @ GPS Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



IIP3 @ GPS Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp



$I_{CC}+I_{REF}$ @ GPS Band in High Gain Mode
 $V_{CC}=3.3V$ and $V_{REF}=3.3V$ Over Temp

